

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-28. (Canceled)

29. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

forming a thin film transistor over a substrate;

forming a first insulating film covering the thin film transistor;

forming a contact hole by etching the first insulating film;

forming a metal wiring on the first insulating film, wherein the metal wiring is electrically connected to the thin film transistor;

forming a second insulating film on the first insulating film and the metal wiring ~~by coating~~;

etching the second insulating film on the metal wiring to expose a surface of the metal wiring wherein the second insulating film has a curved surface at a sidewall portion of the metal wiring; and

forming a pixel electrode on the second insulating film, wherein the pixel electrode is in contact with the metal wiring.

30. (Currently Amended) A method of manufacturing a semiconductor device according to claim 29, wherein the second insulating film is formed by coating and the coating is performed by rotating the substrate at a rotation number of 100 to 2000 rpm.

31. (Original) A method of manufacturing a semiconductor device according to claim 29, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player using a recording medium, digital camera, and a projector.

32. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

forming a thin film transistor and a capacitor element over a substrate;

forming an insulating film covering the thin film transistor and the capacitor element;

forming a contact hole by etching the insulating film;

forming a first metal wiring and a second metal wiring on the insulating film, wherein the first metal wiring and the second metal wiring are electrically connected to the thin film transistor and the capacitor element, respectively;

forming a second insulating film on the first insulating film, on the first metal wiring and on the second metal wiring ~~by coating~~;

etching the second insulating film on the first metal wiring and the second metal wiring to expose a surface of the first metal wiring and the second metal wiring; and

forming a pixel electrode on the second insulating film, wherein the pixel electrode is in contact with the first metal wiring and the second metal wiring.

33. (Currently Amended) A method of manufacturing a semiconductor device according to claim 32, wherein the second insulating film is formed by coating and the coating is performed by rotating the substrate at a rotation number of 100 to 2000 rpm.

34. (Original) A method of manufacturing a semiconductor device according to claim 32, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player using a recording medium, digital camera, and a projector.

35. (Currently Amended) A method of manufacturing a light emitting device, comprising:

forming a thin film transistor and a capacitor element over a substrate;

forming an insulating film covering the thin film transistor and the capacitor element;

forming a contact hole by etching the insulating film;

forming a first metal wiring and a second metal wiring on the insulating film, wherein the first metal wiring and the second metal wiring are electrically connected to the thin film transistor and the capacitor element, respectively;

forming a second insulating film on the first insulating film, on the first metal wiring and on the second metal wiring ~~by coating~~;

etching the second insulating film on the first metal wiring and the second metal wiring to expose a surface of the first metal wiring and the second metal wiring; and

forming a pixel electrode on the second insulating film, wherein the pixel [[30]] electrode is in contact with the first metal wiring and the second metal wiring.

36. (Currently Amended) A method of manufacturing a light emitting device according to claim 35, wherein the second insulating film is formed by coating and the coating is performed by rotating the substrate at a rotation number of 100 to 2000 rpm.

37. (Original) A method of manufacturing a light emitting device according to claim 35, wherein the light emitting device is incorporated in at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player using a recording medium, digital camera, and a projector.

38-49. (Cancelled)

50. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

forming a thin film transistor over a substrate;

forming a first insulating film covering the thin film transistor;

forming a contact hole by etching the first insulating film;

forming a metal wiring on the first insulating film, wherein the metal wiring is electrically connected to the thin film transistor;

forming a second insulating film on the first insulating film and the metal wiring ~~by coating~~, wherein the second insulating film has a lower viscosity than the first insulating film;

etching the second insulating film on the metal wiring to expose a surface of the metal wiring; and

forming a pixel electrode on the second insulating film, wherein the pixel electrode is in contact with the metal wiring.

51. (Currently Amended) A method of manufacturing a semiconductor device according to claim 50, wherein the second insulating film is formed by coating and the coating is performed by rotating the substrate at a rotation number of 100 to 2000 rpm.

52. (Previously Presented) A method of manufacturing a semiconductor device according to claim 50, wherein the second insulating film comprises one or a plurality of kinds of materials selected from the group consisting of polyimide, acrylic resin, polyamide, polyimideamide, and benzocyclobutene.

53. (Previously Presented) A method of manufacturing a semiconductor device according to claim 50, wherein the semiconductor device is at least one selected from the group consisting

of a personal computer, a video camera, a mobile computer, a goggle-type display, a player using a recording medium, digital camera, and a projector.

54. (Currently Amended) A method of manufacturing a light emitting device, comprising:

- forming a thin film transistor over a substrate;
- forming a first insulating film covering the thin film transistor;
- forming a contact hole by etching the first insulating film;
- forming a metal wiring on the first insulating film, wherein the metal wiring is electrically connected to the thin film transistor;
- forming a second insulating film on the first insulating film and the metal wiring ~~by coating~~, wherein the second insulating film has a lower viscosity than the first insulating film;
- etching the second insulating film on the metal wiring to expose a surface of the metal wiring; and
- forming a pixel electrode on the second insulating film, wherein the pixel electrode is in contact with the metal wiring.

55. (Currently Amended) A method of manufacturing a light emitting device according to claim 54, wherein the second insulating film is formed by coating and the coating is performed by rotating the substrate at a rotation number of 100 to 2000 rpm.

56. (Previously Presented) A method of manufacturing a light emitting device according to claim 54, wherein the second insulating film comprises one or a plurality of kinds of materials selected from the group consisting of polyimide, acrylic resin, polyamide, polyimideamide, and benzocyclobutene.

57. (Previously Presented) A method of manufacturing a light emitting device according to claim 54, wherein the light emitting device is incorporated in at least one selected from the

group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player using a recording medium, digital camera, and a projector.

58. (New) A method of manufacturing a semiconductor device according to claim 29, wherein the second insulating film comprises one or a plurality of kinds of materials selected from the group consisting of polyimide, acrylic resin, polyamide, polyimideamide, and benzocyclobutene.

59. (New) A method of manufacturing a semiconductor device according to claim 32, wherein the second insulating film comprises one or a plurality of kinds of materials selected from the group consisting of polyimide, acrylic resin, polyamide, polyimideamide, and benzocyclobutene.

60. (New) A method of manufacturing a light emitting device according to claim 35, wherein the second insulating film comprises one or a plurality of kinds of materials selected from the group consisting of polyimide, acrylic resin, polyamide, polyimideamide, and benzocyclobutene.

61. (New) A method of manufacturing a semiconductor device, comprising:
forming a thin film transistor over a substrate;
forming a first insulating film covering the thin film transistor;
forming a contact hole by etching the first insulating film;
forming a metal wiring on the first insulating film, wherein the metal wiring is electrically connected to the thin film transistor;
forming a second insulating film on the first insulating film and the metal wiring;
etching the second insulating film on the metal wiring to expose a surface of the metal wiring wherein the second insulating film has at least a portion that is thinner than a film thickness of the metal wiring; and

forming a pixel electrode on the second insulating film, wherein the pixel electrode is in contact with the metal wiring.

62. (New) A method of manufacturing a semiconductor device according to claim 61, wherein the second insulating film is formed by coating and the coating is performed by rotating the substrate at a rotation number of 100 to 2000 rpm.

63. (New) A method of manufacturing a light emitting device according to claim 61, wherein the second insulating film comprises one or a plurality of kinds of materials selected from the group consisting of polyimide, acrylic resin, polyamide, polyimideamide, and benzocyclobutene.

64. (New) A method of manufacturing a semiconductor device according to claim 61, wherein the semiconductor device is at least one selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player using a recording medium, digital camera, and a projector.